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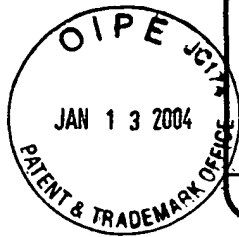
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**Complete if Known**

<b>Application Number</b>	10/693,846
<b>Filing Date</b>	10/20/03
<b>First Named Inventor</b>	August et al.
<b>Group Art Unit</b>	Not Yet Assigned
<b>Examiner Name</b>	Not Yet Assigned
<b>Attorney Docket Number</b>	84,785

Sheet 1 of 2

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Date	
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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet **2**

of **2**

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## **OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS); title of the article (when appropriate); title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	?
		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
		MCGREGOR et al, "Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application IV, vol. 4784 (2002)	
		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosimeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
		GUARINI et al, "Electrical Integrity of State-of-the-Art 0.13 um SOI CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
		ARITA et al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
		HUGHES et al, "Radiation Effects and Hardening of Mos Technology: Devices and Circuits" Preprint IEEE Trans. Nucl. Sci. June 2003	
		LUND et al, "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE Transactions on Nuclear Science, Vol. 33, No. 1, February 1996	
		PETERSEN et al, "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982	
		DAVIS "Use of Computer-Memory Chips as The Basis For a Digital Albedo Neutron Dosimeter*" Health Physics Vol. 49, No. 2 (August), pp. 259-265, 1985 Printed in the U.S.A.	

Examiner  
Signature

Date  
Considered

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